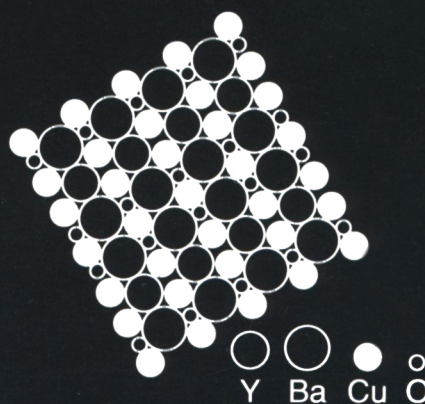
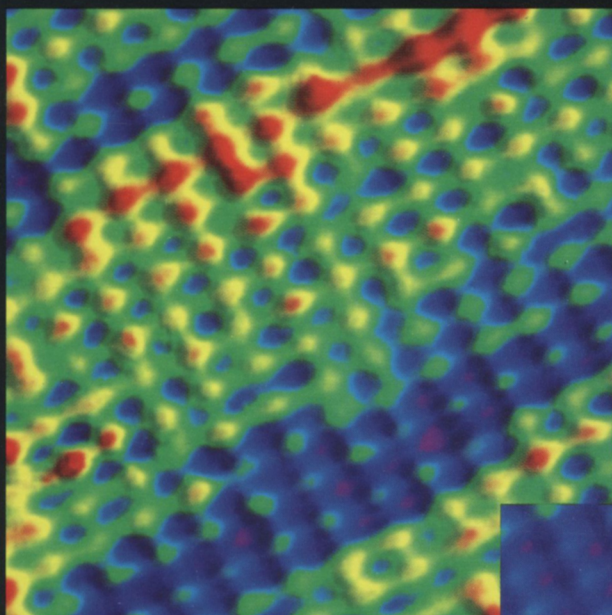


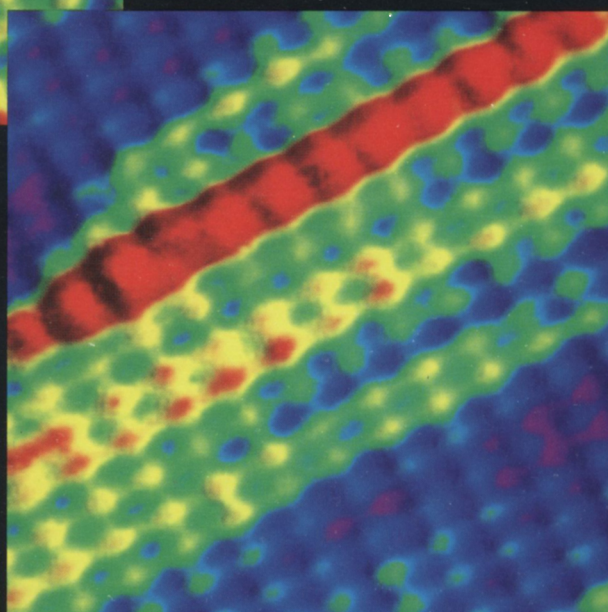
Crystal Engineering of High T_C -Related Oxide Films



$\text{YBa}_2\text{Cu}_3\text{O}_y$ (110) plane

Image Size: 6.5 x 6.5 nm
Current: 0.13 nA
Tip Bias: -1.9 V
Temperature: 4.2 K

Image Size: 6.5 x 6.5 nm
Current: 0.11 nA
Tip Bias: -0.75 V
Temperature: 4.2 K



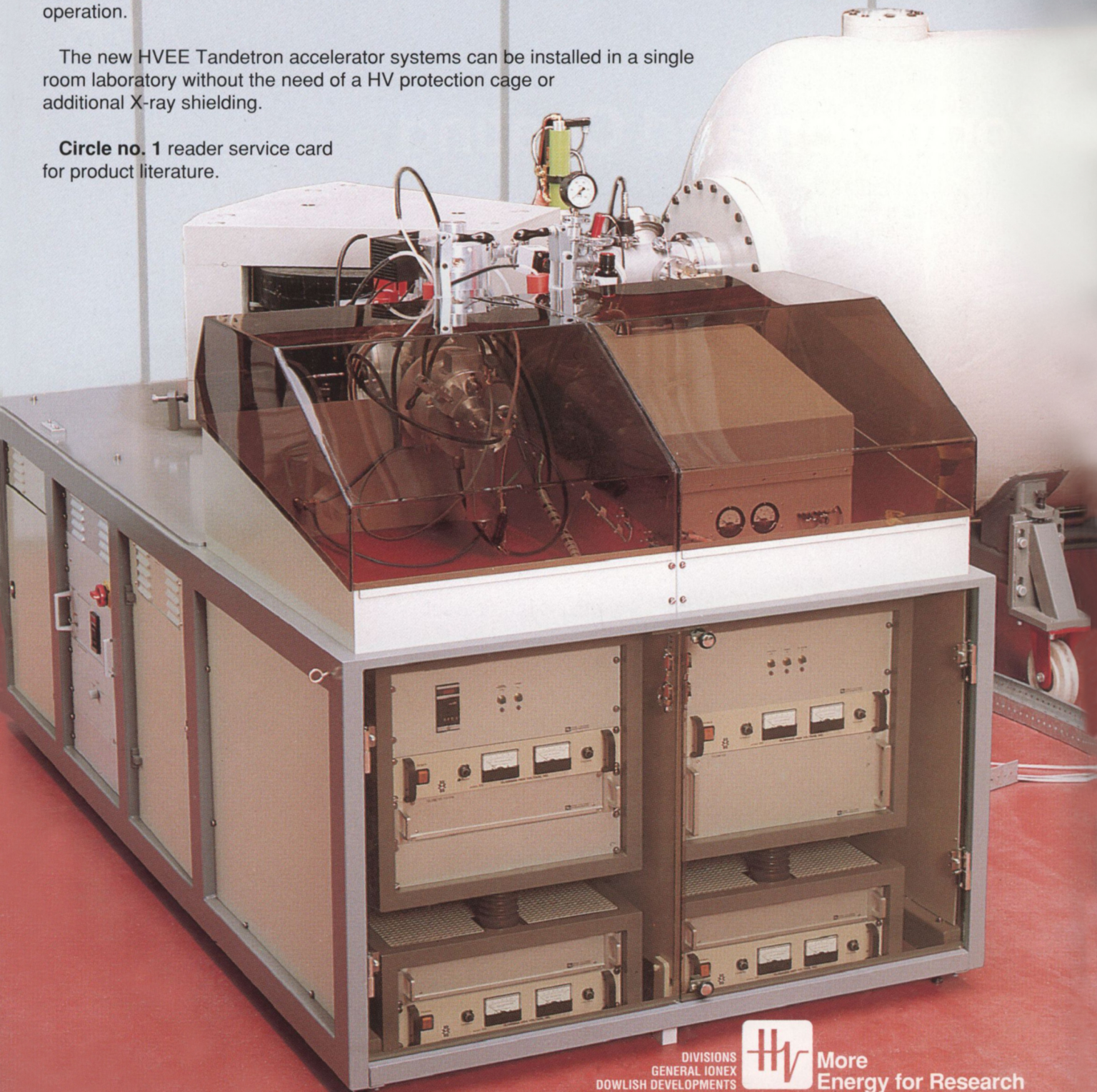
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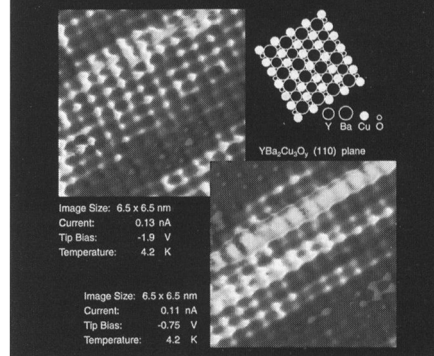
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ON THE COVER: Atomic images of high T_c superconducting $YBa_2Cu_3O_{7-\delta}$ thin film recorded by cryogenic scanning tunneling microscopy. For more about this topic, see "Crystal Growth and Atomic-Level Characterization of $YBa_2Cu_3O_{7-\delta}$ Epitaxial Films" by M. Kawasaki and M. Nantoh on p. 33.

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